



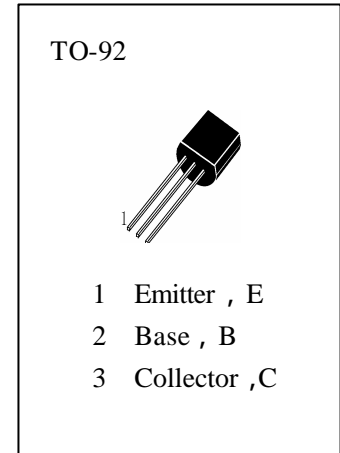
H2222A

APPLICATIONS

General Purpose Transistors.

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg}	Storage Temperature.....	-55~150
T_j	Junction Temperature.....	150
P_C	Collector Dissipation.....	625mW
V_{CBO}	Collector-Base Voltage.....	75V
V_{CEO}	Collector-Emitter Voltage.....	40V
V_{EBO}	Emitter-Base Voltage.....	6V
I_C	Collector Current.....	600mA



ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	75			V	$I_C=10\ \mu A, I_E=0$
BV_{CEO}	Collector-Emitter Breakdown Voltage	40			V	$I_C=10mA, I_B=0$
BV_{EBO}	Emitter-Base Breakdown Voltage	6			V	$I_E=10\ \mu A, I_C=0$
H_{FE}	DC Current Gain	100		400		$V_{CE}=10V, I_C=150mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			0.3	V	$I_C=150mA, I_B=15mA$
I_{CBO}	Collector Cut-off Current			10	nA	$V_{CB}=60V, I_E=0$
I_{EBO}	Emitter Cut-off Current			10	nA	$V_{EB}=3V, I_C=0$
f_t	Current Gain-Bandwidth Product	300			MHz	$V_{CE}=20V, I_C=20mA$
C_{ob}	Output Capacitance			8	pF	$V_{CB}=10V, I_E=0, f=1MHz$